-20V P-CHANNEL ENHANCEMENT MODE MOSFET

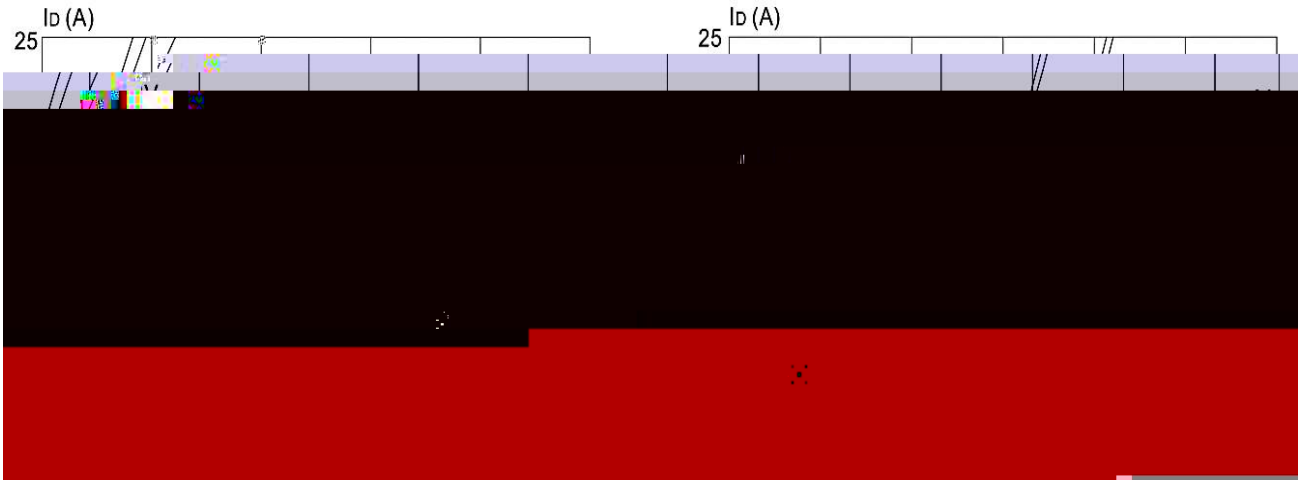
MAIN CHARACTERISTICS

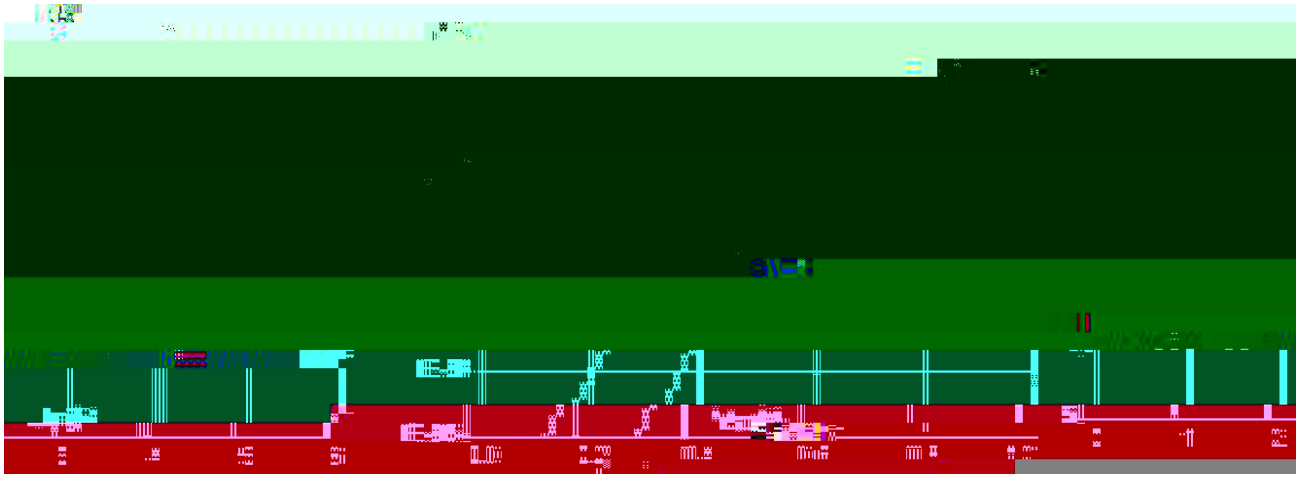
I_D	
V_{DSS}	
R_{DSON}-typ(@V_{GS}=-4.5V)	(Typ: 11 mΩ)
R_{DSON}-typ(@V_{GS}=-2.5V)	(Typ: 15 mΩ)

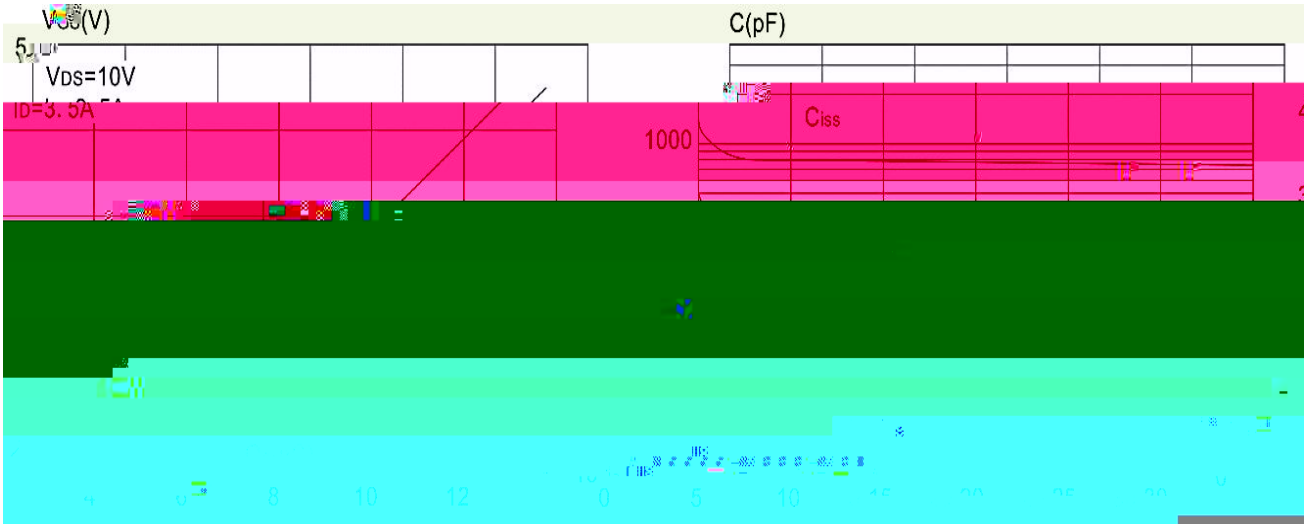
Electrical Characteristics (T_J=25 , unless otherwise noted)

Characteristics	Test Condition	Symbols	Min	Typ	Max	Units
		BV_{DSS}				V
		I_{DSS}				μA
		I_{GSS}				nA
		$V_{GS(th)}$				V
		$R_{DS(ON)}$				mΩ
		C_{iss}				pF
		C_{oss}				
		C_{rss}				
		Q_g				nC
		Q_{gs}				
		Q_{gd}				
		$t_{d(on)}$				ns
		T_r				
		$t_{d(OFF)}$				
		t_f				
		I_S				A
		I_{SM}				A
		V_{SD}				V
		trr				ns
		Qrr				nC

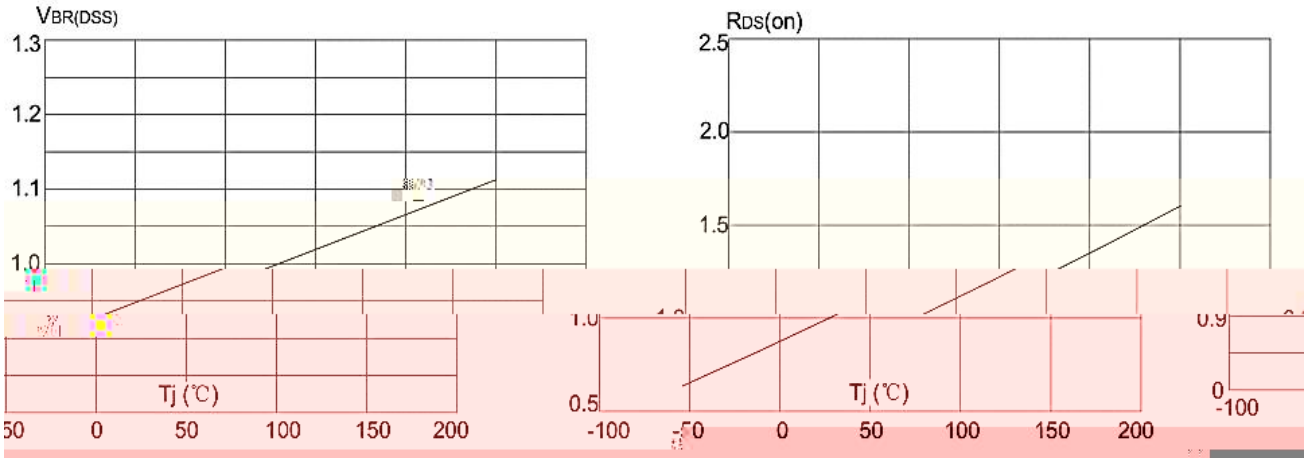
Typical Characteristics

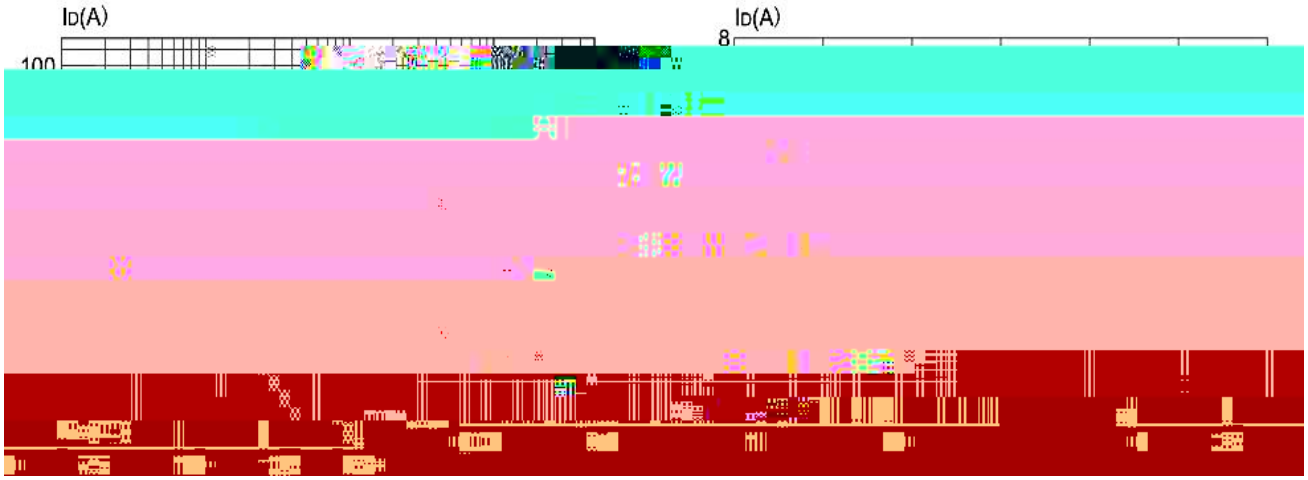


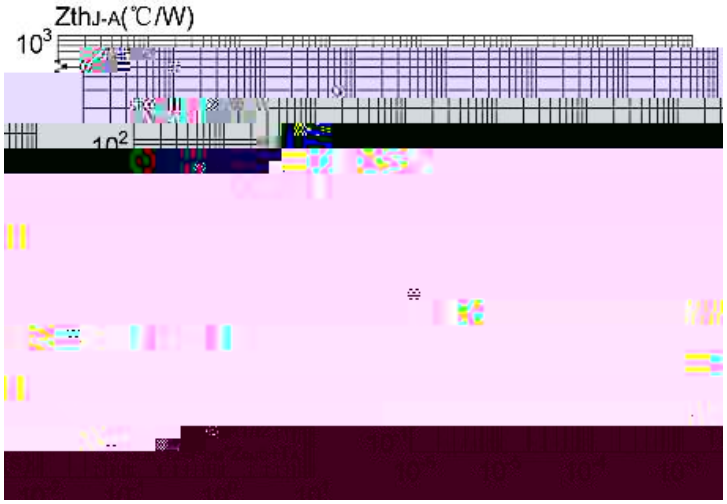


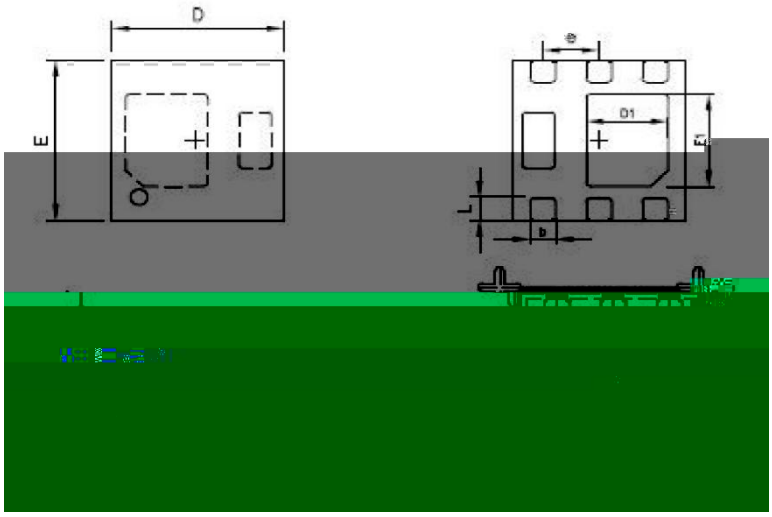


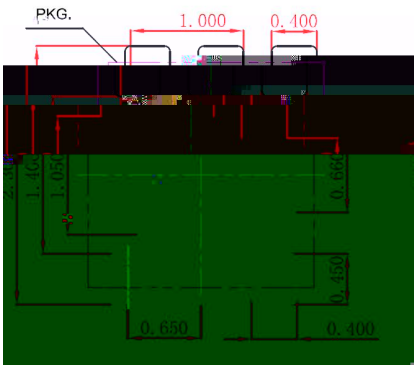
Typical Characteristics








D
E
e
D1
E1
L
b


PKG.
1.000
0.400
1.400
1.050
0.660
0.450
0.650
0.400

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